1	$\overline{+}$	
	•	

Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

				Complete If Known				
	Substitute for	Form 1449A/PTO		Application Number				
	NEODMATIO	N DISCLOSURE		Filing Date	07/14/2003			
•	•••	BY APPLICANT		First Named Inventor	Keith E. Kunz, et al.			
•	PINIEWI	BI APPLICANT		Group Art Unit				
	(use as many sl	heets as necessary)		Examiner Name				
Sheet	1	of	1	Attorney Docket No.	TI-33676.1			

				U.	S. PATENT DOCU	MENTS		
		U.S. Pater	t Document	Name of Patentee	Date of Pub. of Cited Doc. (mm-dd-yyyy)			
Exam. Initials*	Cite 7 No.1	Number	Kind Code ² (if known)	or Applicant of Cited Doc.		Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
MI	, AA	4,692,781		Rountree et al.	09/08/1987			
1/2/1	, AB	4,855,620		Duvvury et al.	08/08/1989			
MI	AC	5,012,317		Rountree	04/30/1991			
M	AD	5,907,462		Chatterjee et al.	05/25/1999			
MI	AE	5,940,258		Duvvury	08/17/1999	257 /909		
	AF							
	AG							
	АН							
	AJ				<u> </u>			
	LA				<u> </u>			

	FOREIGN PATENT DOCUMENTS									
		Fo	reign Patent Do	cument .	Name of Patentee	Date of Pub.				
Exam. Initials*	Cite No. ¹	Office ³	Number ⁴	Kind Code ² (if known)	or Applicant of Cited Doc.	of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Τ°		
	BA									
	BB									
	ВС									
	BD				•					
	BE					<u> </u>				
	BF									
	BG									
	вн									
	BI							_,,,,		
	BJ									

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Exam. Initjats*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MI	CA	Rountree et al., "A Process-Tolerant Input Protection Circuit for Advanced CMOS Processes," 1988 EOS/ESD Symposium, pp. 201-05	
1/2/	СВ	Duvvury et al., "Substrate Pump NMOS for ESD Protection Applications," 2000 EOS/ESD Symposium, Paper 1A.2.1, pp. 7-17	
M	СС	Kunz et al., "5-V Tolerant Fail-safe ESD Solutions for 0.18 um Logic CMOS Process," 2001 ESD/EOS Symposium, September 11, 2001	
	CD		
	CE		
	CF		
	CG		
	СН		
<u>-</u>	CI		ļ
	CJ		

			7	<u> </u>	 				
Examiner						Date	1.10	~ ^1-	
Signature	M	5/0	CSTO	on		Considered	6.10	04	
			•		 				

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²Applicant is to place a check mark here if English Translation is attached.